

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	2299	359/224,290-292,295,298,350,847.ccls.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	14:58
2	BRS	L2	55199	electro-optic\$ or electrooptic\$	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	14:58
3	BRS	L3	703098	silicon	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	14:58
4	BRS	L4	1214717	semiconductor\$2 or semi-conductor\$2	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:00
5	BRS	L5	9592	2 and 3	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:00

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	121	1 and 5	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
7	BRS	L7	357624	membrane\$2	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
8	BRS	L8	638	5 and 7	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
9	BRS	L9	41	1 and 8	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:05 ; IBM_TDB	
10	BRS	L1 0	318125	mars or ((anti-reflect44 or antireflect\$4) near3 switch\$4)	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:08 ; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L1 1	2178	1 not 6	USFAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:06
12	BRS	L1 2	248	2 and 3 and 7 and 10	USFAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:08
13	BRS	L1 3	234	12 not 9	USFAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:19
14	BRS	L1 4	2	goosen-keith\$.in.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:20
15	BRS	L1 5	3	goosen-k\$.in.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L1 6	104	goossen-keith\$.in.	USPAT; US-PGPU B; EPC; 2003/ JPO; 03/20 DERWENT ; IBM_TLB	15:20
17	BRS	L1 7	15	10 and 16	USPAT; US-PGPU B; EPC; 2003/ JPO; 03/20 DERWENT ; IBM_TDB	15:20

	Document ID	Source	Issue Date	Pages	Title	Current OR	Current XRef
1	US 20020109904 A1	US - P G P U B	2002 0815	13	Fast attenuator	359/291	359/290 ; 359/292
2	US 4203128 A	US S P A T	1980 0513	11	Electrostatically deformable thin silicon membranes	331/156	137/891 ; 157/415 ; 157/591 ; 157/E09 .324; 361/291 ; 361/293 .4; 73/77
3	US 5231532 A	US S P A T	1993 0727	8	Switchable resonant filter for optical radiation	359/295	359/294; 359/578 ; 359/586 ; 359/589
4	US 5506919 A	US S P A T	1996 0409	12	Conductive membrane optical modulator	385/1	385/2; 385/23
5	US 5510277 A	US S P A T	1996 0423	11	Surface treatment for silicon substrates	438/707	134/1.3 ; 438/974
6	US 5943155 A	US S P A T	1999 0824	13	Mars optical modulators	359/247	359/290 ; 359/291 ; 359/295 ; 359/318

	Document ID	Source	Issue Date	Pages	Title	Current OR	Current XRef
7	US 5943155 A	<input checked="" type="checkbox"/> DEPENDENT	1999 0824	13	Double poly mechanical antireflection switch (MARS) device for optical modulators		
8	US 5943158 A	<input checked="" type="checkbox"/> US PAT	1999 0824	15	Micro-mechanical, anti-reflection, switched optical modulator array and fabrication method	359/295	359/290 ; 359/291 ; 359/318 ; 359/223
9	US 5949571 A	<input checked="" type="checkbox"/> US PAT	1999 0907	13	Mars optical modulators	359/291	; 359/290 ; 359/295 ; 359/318 ; 430/321
10	US 6337753 B1	<input checked="" type="checkbox"/> US PAT	2002 0108	8	Optical power equalizer	359/124	359/290 ; 359/291
11	US 6462858 B1	<input checked="" type="checkbox"/> US PAT	2002 1008	11	Fast attenuator	359/290	359/237 ; 359/291 ; 359/295 ; 359/347
12	US 6519073 B1	<input checked="" type="checkbox"/> US PAT	2003 0211	16	Micromechanical modulator and methods for fabricating the same	359/290	359/248 ; 359/291